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Table of Contents

Session I. PLENARY SESSION

1-12

- I.-1 **Mapping a Path to the Beyond-CMOS Technology for Computation** *****
8:50 AM I. A. Young, Components Research, Intel Corporation, Hillsboro, Oregon, USA
- I.-2 **Solid-State Electronics and Single-Molecule Biophysics** 7
10:10A M K. Shepard, Department of Electrical Engineering, Columbia University, New York, New York, USA
- I.-3 **Advanced Device Technologies for Defense Systems** 9
11:10 AM J. C. Zolper, Raytheon Company, Waltham, Massachusetts, USA

Session II.A. MEMS, SENSORS and HARVESTORS

13-24

- II.A-1 **High performance miniaturized NEMS sensors Toward co-integration with CMOS?** 15
1:30 PM T. Ernst, J. Arcamone, J. Philippe, O. Martin, E. Ollier, P. Batude, V. Gouttenoire, C. Marcoux, F. Ricoul, C. Dupré, E. Colinet, O. Rozeau, G. Billiot, and L. Duraffourg, CEA, LETI, MINATEC Campus, Grenoble, FRANCE
- II.A-2 **Silicon Monolithic MEMS + Photonic Systems** 17
2:10 PM S. A. Bhawe, OxideMEMS Lab, Cornell University, Ithaca, New York, USA
- II.A-3 **Highly Sensitive III-V Nitride Based Piezoresistive Microcantilever Using Embedded AlGaIn/GaN HFET as Ultrasonic Detector** 19
2:50 PM A. Talukdar¹, M. Qazi², and G. Koley¹, ¹University of South Carolina, Columbia, South Carolina, USA and ²Intel Corp., Portland, Oregon, USA
- II.A-4 **Nanostructured thermoelectric energy conversion and refrigeration devices** 21
3:30 PM A. Shakouri, Birck Nanotechnology Center, Purdue University, West Lafayette, Indiana, USA
- II.A-5 **Piezotronics and Piezo-phototronics** 23
4:10 PM Z. L. Wang, School of Materials Science and Engineering, Georgia Institute of Technology, Atlanta, Georgia, USA
- II.A-6 **Alternative Graphene Devices: Beyond Field Effect Transistors** 24a
4:50 PM M.C. Lemme, S. Vaziri, A.D. Smith, M. Ostling KTH Royal Institute of Technology, Sweden

Session II.B. ALTERNATE TRANSISTOR CONCEPT

25-38

- II.B-1 **Novel Double Layer Graphene Transistors-Bilayer Pseudospin FETs and 2D-2D Tunnel FETs** 27
1:30 PM S. K. Banerjee¹, L. F. Register¹, E. Tutuc¹, D. Reddy¹, S. Kim¹, D. Basu¹, C. Corbet¹, L. Colombo², G. Carpenter³ and A. H. MacDonald¹, ¹University of Texas at Austin, ²Texas Instruments, Incorporated, Dallas, Texas, USA, and ³IBM Research, Austin, Texas, USA
- II.B-2 **Effect of Interfacial Phonon-Plasmon Modes on Electrical Transport in Supported Graphene** 29
2:10 PM Z.-Y. Ong and M. V. Fischetti, Department of Materials Science and Engineering, University of Texas at Dallas, Richardson, Texas, USA
- II.B-3 **Possible Applications of Topological Insulator Thin Films for Tunnel FETs** 31
2:30 PM J. Chang, L. F. Register, and S. K. Banerjee, Microelectronics Research Center, The University of Texas at Austin, Austin, Texas, USA
- II.B-4 **SymFET: A Proposed Symmetric Graphene Tunneling Field Effect Transistor** 33
2:50 PM P. Zhao¹, R. M. F. Feenstra², G. Gu³ and D. Jena¹, ¹Department of Electrical Engineering, University of Notre Dame, Notre Dame, Indiana, USA, ²Dept. Physics, Carnegie Mellon University, Pittsburgh, Pennsylvania, USA and ³Dept. Electrical Engineering and Computer Science, University of Tennessee, Knoxville, Tennessee, USA

- II.B-5 **Hybrid straintronics and spintronics: An ultra energy-efficient paradigm for logic and memory** 35
3:30 PM S. Bandyopadhyay¹ and J. Atulasimha², ¹Department of Electrical and Computer Engineering and ²Department of Mechanical and Nuclear Engineering, Virginia Commonwealth University, Richmond, Virginia, USA
- II.B-6 **Graphene and Topological Insulator Based Transistors: Beyond Computing Applications** 37
4:10 PM Y. P. Chen, Department of Physics and Birck Nanotechnology Center and School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA
- II.B-7 **Late News**
4:50 PM

Session III. Poster Session

39-148

- III-1 **Al₂O₃/InSb/Si Quantum Well MOSFETs Having an Ultra-Thin InSb Layer** 45
K. Maezawa¹, T. Ito¹, A. Kadoda¹, K. Nakayama¹, Y. Yasui¹, M. Mori¹, E. Miyazaki² and T. Mizutani², ¹University of Toyama, Gofuku, Toyama, JAPAN and ²Nagoya University, Furo-cho, Chikusa-ku, Nagoya, JAPAN
- III-2 **Ultra-Sensitive Magnetoelectric Sensor with High Saturation Field** 47
L. Mei, Z. Fang, F. Li, S. Datta, and Q. M. Zhang, Department of Electrical Engineering, The Pennsylvania State University, University Park, Pennsylvania, USA
- III-3 **Study of SiO_x-based Complementary Resistive Switching Memristor** 49
Y.-F. Chang¹, Y.-T. Chen¹, F. Xue¹, Y. Wang¹, F. Zhou¹, B. Fowler², and J. C. Lee¹, ¹Microelectronics Research Center, Department of Electrical and Computer Engineering, The University of Texas at Austin, Austin, Texas, USA and ²PrivaTran, LLC, Austin, Texas, USA
- III-4 **Illumination Instability Analysis of ZnO Thin Film Transistors with HfO₂ Gate Dielectrics** 51
J. J. Siddiqui¹, J. D. Phillips¹, K. Leedy², and B. Bayraktaroglu², ¹EECS Department, University of Michigan, Ann Arbor, Michigan, USA and ²Air Force Research Laboratory, Sensors Directorate, Wright-Patterson AFB, Ohio, USA
- III-5 **1.4 kV Breakdown Voltage for MOCVD grown AlGaIn/GaN HEMTs on Si substrate** 53
S. . Selvaraj, A. Watanabe, A. Wakejima and T. Egawa, Research Center for Nano-Device and System, Nagoya Institute of Technology, Showa-ku, Nagoya, JAPAN
- III-6 **Dopant Straggle-free Heterojunction Intra-band Tunnel (HIBT) FETs with Low Drain-induced Barrier Lowering/Thinning (DIBL/T) and Reduced Variation in OFF Current** 55
S. K. Gupta¹, J. P. Kulkarni², S. Datta³ and K. Roy¹, ¹Purdue University, West Lafayette Indiana, USA, ²Intel Corporation, Hillsboro, Oregon, USA and ³Penn State University, University Park, Pennsylvania, USA
- III-7 **Exclusive Electrical Determination of High-Resistance Grain-Boundaries in poly-Graphene** 57
R Chen^{1,2}, S. R. Das¹, C Jeong¹, D. B. Janes¹, M. A. Alam¹, ¹Purdue University, West Lafayette, Indiana, USA and ²Zhejiang University, Zhejiang, CHINA
- III-8 **Improved OFF-state Breakdown Voltage in AlGaIn/GaN HEMTs grown on 150-mm Diameter Silicon-on-Insulator (SOI) Substrate** 59
S. Arulkumar¹, V. K. X. Lin², S. B. Dolmanan², G.I. Ng³, S. Vicknesh¹, J. P. Y. Tan², S. L. Teo², M. K. Kumar² and S. Tripathy², ¹Temasek Laboratories@NTU, Nanyang Technological University, SINGAPORE, ²Institute of Materials Research and Engineering, A*STAR, SINGAPORE, and ³NOVITAS, Nanoelectronics Centre of Excellence, School of EEE, Nanyang Technological University, SINGAPORE
- III-9 **Improved Dual-Carrier High Gain Impact Ionization Engineered Avalanche Photodiode** 61
J. Huang¹, K. Banerjee¹, S. Ghosh¹, and M. M. Hayat², ¹Dept. of ECE, Univ. of Illinois at Chicago, Chicago, Illinois, USA and ²Center for High Technology Materials, Univ. of New Mexico, Albuquerque, New Mexico, USA
- III-10 **Enhanced Tunneling Current in 1d-1d_{Edge} Overlapped TFET's** 63
S. Agarwal and E. Yablonovitch, University of California, Berkeley, California, USA

- III-11 **Metal Contacts to Mo₂: a Two-Dimensional Semiconductor 65**
A. T. Neal, H. Liu, J. J. Gu, and P. D. Ye, School of Electrical and Computer Engineering and Birck Nanotechnology Center, Purdue University, West Lafayette, Indiana, USA
- III-12 **Balancing stress & dipolar interactions for fast, low power, reliable switching in multiferroic logic 67**
K. Munira, S. Nadri, M. Forgues, and A. W. Ghosh, Department of Electrical and Computer Engineering, University of Virginia, Charlottesville, Virginia, USA
- III-13 **Double Slot High-k Waveguide Grating Couplers for Silicon Photonics 69**
M. M. Naiini, C. Henkel, G. B. Malm and M. Östling, KTH Royal Institute of Technology, School of Information and Communication Technology, Integrated Devices and Circuits, Kista, SWEDEN
- III-14 **Self-aligned metal S/D GaSb p-MOSFETs using Ni-GaSb alloys 71**
C. B. Zota, S. H. Kim, Y. Asakura, M. Takenaka and S. Takagi, School of Engineering, The University of Tokyo, Bunkyo-ku, Tokyo, JAPAN
- III-15 **Bilayer Graphene Vertical Tunneling Field Effect Transistor 73**
D. Reddy, L. F. Register, and S. K. Banerjee, University of Texas, Austin, Texas, USA
- III-16 **440 V AlSiN-Passivated AlGaIn/GaN High Electron Mobility Transistor with 40 GHz Bandwidth 75**
E. Harvard and J. R. Shealy, Cornell University, School of Electrical and Computer Engineering, Ithaca, New York, USA
- III-17 **Analysis of terahertz zero bias detectors by using a triple-barrier resonant tunneling diode integrated with a self-complementary bow-tie antenna 77**
M. Suhara¹, S. Takahagi¹, K. Asakawa¹, T. Okazaki¹, M. Nakamura¹, S. Yamashita¹, Y. Itagaki¹, M. Saito¹, A. Tchegho², G. Keller², A. Poloczek², W. Prost², F.-J. Tegud², ¹Electrical and Electronic Engineering, Graduate School of Science and Engineering, Tokyo Metropolitan University, Hachioji, Tokyo, JAPAN and ²Center for Semiconductor Technology and Optoelectronics, University of Duisburg-Essen, Duisburg, GERMANY
- III-18 **An InAs Nanowire Spin Transistor with Subthreshold Slope of 20mV/dec 79**
K. Yoh¹, Z. Cui¹, K. Konishi¹, M. Ohno², K. Blekker³, W. Prost³, F.-J. Tegude³, J.-C. Harmand⁴, ¹Research Center for Integrated Quantum Electronics, Hokkaido University, Sapporo, JAPAN, ²Graduate School of Engineering, Hokkaido University, Sapporo, JAPAN, ³Semiconductor and Information Engineering, University of Duisburg-Essen, Duisburg, GERMANY, and ⁴CNRS-Laboratory of Photonic and Nanostructures, Marcoussis, FRANCE
- III-19 **Understanding dual-gate polymer field-effect transistors 81**
T.-J. Ha¹, P. Sonar² and A. Dodabalapur¹, ¹Microelectronics Research Center, The University of Texas at Austin, Austin, Texas, USA and ²Institute of Materials Research and Engineering, Singapore, SINGAPORE
- III-20 **Fundamental Limitations of Conventional-FET Biosensors: Quantum-Mechanical-Tunneling to the Rescue 83**
D. Sarkar and K. Banerjee, Department of Electrical and Computer Engineering, University of California, Santa Barbara, California, USA
- III-21 **Can Quasi-Saturation in the Output Characteristics of Short-Channel Graphene Field-Effect Transistors be Engineered? 85**
K. Ganapathi¹, M. Lundstrom² and S. Salahuddin¹, ¹Department of Electrical Engineering and Computer Sciences, UC Berkeley, Berkeley, California, USA and ²School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA
- III-22 **Phonon Limited Transport in Graphene Pseudospintronic Devices 87**
Z. J. Estrada, B. Dellabatta, U. Ravaioli, and M. J. Gilbert, University of Illinois at Urbana-Champaign, Urbana, Illinois, USA
- III-23 **Resistive Switching in Aluminum Nitride 89**
M. J. Marinella, J. E. Stevens, E. M. Longoria, and P. G. Kotula, Sandia National Laboratories, Albuquerque, New Mexico, USA

- III-24 **Limits of Detection for Silicon Nanowire BioFETs 91**
N. K. Rajan, X. Duan, A. Vacic, D. A. Routenberg, and M. A. Reed, Dept. of Applied Physics, Dept. of Electrical Engineering, New Haven, Connecticut, USA
- III-25 **Hole-blocking TiO₂/Silicon Heterojunction for Silicon Photovoltaics 93**
S. Avasthi¹, W. McClain², J. Schwartz², and J. C. Sturm¹, Princeton Institute for the Science and Technology of Materials, ¹Department of Electrical Engineering and ²Department of Chemistry, Princeton University, Princeton New Jersey, USA
- III-26 **Recess Integration of Platelet Laser Diodes with Waveguides on Silicon 95**
S. Famenini and C. G. Fonstad, Massachusetts Institute of Technology, Cambridge, Massachusetts, USA
- III-27 **NLSTT-MRAM: Robust Spin Transfer Torque MRAM using Non-Local Spin Injection for Write 97**
M. Sharad¹, G. Panagopoulos¹, C. Augustine² and K. Roy¹, ¹School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA and ²Circuit Research Lab, Intel Corporation, Hillsboro, Oregon, USA
- III-28 **All Spin Logic device as a compact artificial neuron 99**
A. Sarkar¹, B. Behin-Aein², S. Srinivasan¹, and S. Datta¹, ¹School of Electrical and Computer Engineering, Purdue University, W. Lafayette, Indiana, USA and ²Technology Research Group, GLOBALFOUNDRIES USA, Sunnyvale, California, USA
- III-29 **Experimental Demonstration of “Cold” Low Contact Resistivity Ohmic Contacts on Moderately Doped n-Ge with in-situ Atomic Hydrogen Clean 101**
A. Agrawal¹, J. Park², D. Mohata¹, K. Ahmed² and S. Datta¹, ¹Department of Electrical Engineering, The Pennsylvania State University, University Park, Pennsylvania, USA and ²Applied Materials, Inc., Santa Clara, California, USA
- III-30 **Mobility and Scattering Mechanisms in Buried InGaSb Quantum Well Channels Integrated with in-situ MBE Grown Gate Oxide 103**
S. Madiseti, P. Nagaiah, T. Chidambaram, V. Tokranov, M. Yakimov, and S. Oktyabrsky, College of Nanoscale Science and Engineering, University at Albany- SUNY, Albany, New York, USA
- III-31 **Dielectric Thickness Dependence of Quantum Capacitance in Graphene Varactors with Local Metal Back Gates 105**
M. A. Ebrish and S. J. Koester, University of Minnesota-Twin Cities, Minneapolis, Minnesota, USA
- III-32 **Negative differential resistance in short-channel graphene FETs: semianalytical model and simulations 107**
R. Grassi¹, T. Low², A. Gnudi¹ and G. Baccarani¹, ¹ARCES, University of Bologna, Bologna, ITALY and ²IBM T. J. Watson Research Center, Yorktown Heights, New York, USA
- III-33 **Drain-Induced-Barrier Lowering and Subthreshold Swing Fluctuations in 16-nm-Gate Bulk FinFET Devices Induced by Random Discrete Dopants 109**
H.-W. Su, Y. Li, Y.-Y. Chen, C.-Y. Chen, and H.-T. Chang, Parallel and Scientific Computing Laboratory, Department of Electrical Engineering, National Chiao Tung University, Hsinchu, TAIWAN
- III-34 **THz Detector Based on Proximity Effect of Topological Insulator 111**
X. Li, Y. G. Semenov, and K. W. Kim, Dept. of Electrical and Computer Engineering, North Carolina State University, Raleigh, North Carolina, USA
- III-35 **Transverse-Field Bandgap Modulation on Graphene Nanoribbon Transistors by Double-Self-Aligned Spacers 113**
L.-T. Tung, M. V. Mateus and E. C. Kan, School of Electrical and Computer Engineering, Cornell University, Ithaca, New York, USA
- III-36 **Epitaxial Si Punch-Through based Selector for Bipolar RRAM 115**
P. Bafna¹, P. Karkare¹, S. Srinivasan¹, S. Chopra², S. Lashkare¹, Y. Kim², S. Srinivasan², S. Kuppura², S. Lodha¹, and U. Ganguly¹, ¹Department of Electrical Engineering, Indian Institute of Technology, Bombay, Mumbai, INDIA and ²Epi-Division, Front End Products, Applied Materials Inc., Santa Clara, California, USA

- III-37 **A Figure of Merit for Oscillator-Based Thin-Film Circuits on Plastic for High-Performance Signaling, Energy Harvesting and Driving of Actuation Circuits 117**
W. Rieutort-Louis, L. Huang, Y. Hu, J. Sanz-Robinson, S. Wagner, J. C. Sturm, and N. Verma, Princeton University, Department of Electrical Engineering, Princeton, New Jersey, USA
- III-38 **Short-Channel Enhancement-mode Planar GaAs Nanowire HEMTs through a Bottom-up method 119**
X. Miao, C. Zhang and X. Li, Department of Electrical and Computer Engineering, Micro and Nanotechnology Laboratory, University of Illinois at Urbana-Champaign, Urbana, Illinois, USA
- III-39 **Electric Field Driven Domain Wall Transfer in Hybrid Structures 121**
X. Duan¹, V. Stephanovich², Y. G. Semenov¹, H. Fangohr³, M. Franchin³, and K. W. Kim¹, ¹Electrical and Computer Engineering, North Carolina State University, Raleigh, North Carolina, USA, ²Institute of Physics, Opole University, Oleska, POLAND and ³Engineering and the Environment, University of Southampton, Southampton, UNITED KINGDOM
- III-40 **Comparison of Graphene Nanoribbons With Cu and Al Interconnects 123**
N. Wang¹, C. D. English², and E. Pop¹, ¹Dept. of Electrical and Computer Engineering and ²Dept. of Physics, University of Illinois at Urbana-Champaign, Urbana, Illinois, USA
- III-41 **Electrical Control of Nuclear-Spin-Induced Hall Voltage in an Inverted InAs Heterostructure 125**
T. Ishikura, Z. Cui and K. Yoh, Research Center of Integrated Quantum Electronics, Hokkaido University, Sapporo, JAPAN
- III-42 **Epitaxially defined (ED) FinFET: to reduce V_T variability and enable multiple V_T 127**
S. Mittal¹, S. Gupta², A. Nainani², M.C. Abraham², K. Schuegraf², S. Lodha¹, U. Ganguly¹, ¹CEN, Department of EE, Indian Institute of Technology Bombay, INDIA and ²Applied Materials Inc, Santa Clara, California, USA
- III-43 **Power Reduction in Nanomagnetic Logic Clocking through High Permeability Dielectrics 129**
P. Li¹, G. Csaba¹, V. K. Sankar¹, X. S. Hu², M. Niemier², W. Porod¹, and G. H. Bernstein¹, ¹Department of Electrical Engineering and ²Department of Computer Science and Engineering, University of Notre Dame, Notre Dame, Indiana, USA
- III-44 **New Tunnel-FET Architecture with Enhanced I_{ON} and Improved Miller Effect for Energy Efficient Switching 131**
A. Biswas, C. Alper, L. De Michielis, A. M. Ionescu, Nanoelectronics Devices Laboratory (NANOLAB), Ecole Polytechnique Fédérale de Lausanne, EPFL, SWITZERLAND
- III-45 **Switching dynamics in ferroelectric-charge hybrid nonvolatile memory 133**
K. Auluck, S. Rajwade and E. C. Kan, School of Electrical and Computer Engineering, Cornell University, Ithaca, New York, USA
- III-46 **Frequency Dependence of Amorphous Silicon Schottky Diodes for Large-Area Rectification Applications 135**
J. Sanz-Robinson, W. Rieutort-Louis, N. Verma, S. Wagner, and J. C. Sturm, Dept. of Electrical Engineering and the Princeton Institute for the Science and Technology of Materials, Princeton University, Princeton, New Jersey, USA
- III-47 **Reliability Improvement Achieved by N_2O Radical Treatment for AlGaIn/GaN Heterojunction Field-Effect Transistors 137**
C.-Y. Hu and T. Hashizume, Research Center for Integrated Quantum Electronics (RCIQE), Hokkaido University, Sapporo, JAPAN
- III-48 **Exploring Variability and Reliability of Multi-Level STT-MRAM Cells 139**
G. Panagopoulos¹, C. Augustine², X. Fong¹ and K. Roy¹, ¹School of ECE, Purdue University, West Lafayette, Indiana, USA and ²Circuit Research Lab, Intel labs, Hillsboro, Oregon, USA
- III-49 **Comparative Study of LEDs conformally overgrown on multi-facet GaN NWs vs. conventional c-plane LEDs 141**
A..M. Hosalli¹, P. Frajttag², D. M. Van Den Broeck¹, T. Paskova¹, N..A. El-Masry², and S..M. Bedair¹, ¹Department of Electrical and Computer Engineering, North Carolina State University, Raleigh, North Carolina, USA and ²Department of Materials Science and Engineering, North Carolina State University, Raleigh, North Carolina, USA

- III-50 **Inkjet-printed SWCNT films for stretchable electrode and strain sensor applications** 143
T. Kim, J. Byun, H. Song and Y. Hong, Department of Electrical Engineering and Computer Science, Seoul National University, Gwanak-gu, Seoul, KOREA
- III-51 **Comparison of Instantaneous Crystallization and Metastable Models in Phase Change Memory Cells** 145
A. Faraclas, N. Williams, G. Bakan, A. Gokirmak, and H. Silva, Electrical and Computer Engineering, University of Connecticut, Storrs, Connecticut, USA
- III-52 **A Surface-Potential Based Compact Model for GaN HEMTs Incorporating Polarization Charges** 147
R. Jana and D. Jena, Electrical Engineering, University of Notre Dame, Notre Dame, Indiana, USA

Session IV.A. Wide Bandgap/High Speed Devices 149-170

- IV.A-1 **N-polar GaN/InAlN MIS-HEMT with 400-GHz f_{max}** 151
8:20 D. Denninghoff, J. Lu, M. Laurent, E. Ahmadi, S. Keller and U. K. Mishra, Department of Electrical and Computer Engineering, University of California, Santa Barbara, California, USA
- IV.A-2 **Ultra-thin Body GaN-on-Insulator nFETs and pFETs: Towards III-Nitride Complementary Logic** 153
8:40 G. Li, R. Wang, J. Verma, H. Xing, D. Jena, Department of Electrical Engineering, University of Notre Dame, Notre Dame, Indiana, USA
- IV.A-3 **Improved GaN-based HEMT Performance by Nanocrystalline Diamond Capping** 155
9:00 AM T. J. Anderson¹, K. D. Hobart¹, M. J. Tadjer², T. I. Feygelson³, E. A. Imhoff¹, D. J. Meyer¹, D. S. Katzer¹, J. K. Hite¹, F. J. Kub¹, B. B. Pate¹, S. C. Binari¹, and C. R. Eddy, Jr¹, ¹ Naval Research Laboratory, Washington District of Columbia, USA, ² Universidad Politécnica de Madrid, Madrid, SPAIN and ³ SAIC, Inc., Washington, District of Columbia, USA
- IV.A-4 **Record low tunnel junction specific resistivity (< 3X10⁻⁴ Ohm-cm²) in GaN inter-band tunnel junctions** 157
9:20 AM S. Krishnamoorthy¹, F. Akyol¹, J. Yang², P. S. Park¹, R. C. Myers^{2,1}, S. Rajan^{1,2}, ¹Department of Electrical & Computer Engineering, The Ohio State University, Columbus, Ohio, USA and ²Department of Material Science & Engineering, The Ohio State University, Columbus, Ohio, USA
- IV.A-5 **Ga₂O₃ Schottky barrier diodes fabricated on single-crystal β-Ga₂O₃ substrates** 159
9:40 AM K. Sasaki^{1,2}, M. Higashiwaki^{2,3}, A. Kuramata¹, T. Masui⁴, and S. Yamakoshi¹, ¹Tamura Corporation, Sayama, Saitama, JAPAN, ²National Institute of Information and Communications Technology, Koganei, Tokyo, JAPAN, ³PRESTO, Japan Science and Technology Agency, Chiyoda, Tokyo, JAPAN, and ⁴Koha Co., Ltd., Nerima, Tokyo, JAPAN
- IV.A-6 **Quaternary nitride enhancement mode HFET with 260 mS/mm and a threshold voltage of +0.5 V** 161
10:20 AM N. Ketteniss¹, B. Reuters¹, B. Holländer², H. Hahn¹, H. Kalisch¹, and A. Vescan¹, ¹GaN Device Technology, RWTH Aachen University, Aachen, GERMANY and ²Forschungszentrum Juelich GmbH, Juelich, GERMANY
- IV.A-7 **Methods for Attaining High Interband Tunneling Current in III-Nitrides** 163
10:40 AM T. A. Growden, S. Krishnamoorthy, D. N. Nath, A. Ramesh, S. Rajan, and P. R. Berger, Department of Electrical and Computer Engineering, The Ohio State University, Columbus, Ohio, USA
- IV.A-8 **Experimental Demonstration of a Wafer-Bonded Heterostructure based Unipolar Transistor with In_{0.53}Ga_{0.47}As Channel and III-N Drain** 165
11:00 AM S. Lal¹, J. Lu¹, B. Thibeault¹, S. P. Denbaars², and U. K. Mishra¹, ¹Department of Electrical and Computer Engineering and ²Materials Department, University of California, Santa Barbara, California, USA
- IV.A-9 **Electrical Evidence of Disorder at the SiO₂/4H-SiC MOS Interface and its Effect on Electron Transport** 167
11:20 AM S. Swandono, A. Penumatcha, and J. A. Cooper, School of Electrical and Computer Engineering and Birck Nanotechnology Center, Purdue University, West Lafayette, Indiana, USA
- IV.A-10 **Asymmetric Dual-Grating Gate InGaAs/InAlAs/InP HEMTs for Ultrafast and Ultrahigh Sensitive Terahertz Detection** 169
11:40 AM S. Boubanga-Tombet¹, Y. Tanimoto¹, T. Watanabe¹, T. Suemitsu¹, W. Yuye², H. Minamidev², H. Ito², V. Popov³, and T. Otsuji¹, ¹Research Institute of Electrical Communication, Tohoku University, Aoba-Ku, Sendai, JAPAN, ²RIKEN Sendai, Aoba-ku, Sendai, JAPAN, and ³Institute of Radio Engineering and Electronics (Saratov Branch), Saratov, RUSSIA

- IV.B-1 **Role of Screening, Heating, and Dielectrics on High-Field Transport in Graphene** 173
8:20 AM A. Y. Serov, Z.-Y. Ong, V. E. Dorgan and E. Pop, Dept. of Electrical and Computer Engineering, University of Illinois, Urbana-Champaign, Illinois, USA and Micro and Nanotechnology Lab, Urbana Illinois, USA
- IV.B-2 **Graphene field-effect transistors with self-aligned spin-on-doping of source/drain access regions** 175
8:40 AM H. C. P. Movva¹, M. E. Ramón¹, C. M. Corbet¹, F. S. Chowdhury¹, G. Carpenter², E. Tutuc¹, and S. K. Banerjee¹, ¹Microelectronics Research Center, The University of Texas at Austin, Texas, USA and ²IBM Research, Austin, Texas, USA
- IV.B-3 **High Performance, Large Area Graphene Transistors on Quasi-Free-Standing Graphene Using Synthetic Hexagonal Boron Nitride Gate Dielectrics** 177
9:00 AM M. J. Hollander, A. Agrawal, M. S. Bresnehan, M. LaBella, K. A. Trumbull, R. Cavalero, S. Datta, and J. A. Robinson, The Pennsylvania State University, University Park, Pennsylvania, USA
- IV.B-4 **MoS₂-based devices and circuits** 179
9:20 AM B. Radisavljevic, D. Krasnozhan, M.B. Whitwick, and A. Kis, Electrical Engineering Institute, School of Engineering, EPFL, Lausanne, SWITZERLAND
- IV.B-5 **Extraction of Near Interface Trap Density in Top Gated Graphene Transistor Using High Frequency Current Voltage Characteristics** 181
10:20 AM H. Madan¹, M. J. Hollander¹, J. A. Robinson², and S. Datta¹, ¹Electrical Engineering, The Pennsylvania State University, University Park, Pennsylvania, USA and ²Material Science and Engineering, The Pennsylvania State University, University Park, Pennsylvania, USA
- IV.B-6 **Pulsed Nanosecond Characterization of Graphene Transistors** 183
10:40 AM E. Carrion, A. Malik, A. Behnam, S. Islam, F. Xiong and E. Pop, Dept. of Electrical and Computer Engineering, University of Illinois, Urbana-Champaign, Illinois, USA and Micro and Nanotechnology Lab, Urbana Illinois, USA
- IV.B-7 **Graphene Nanomesh Contacts and Its Transport Properties** 185
11:00 AM T. Chu and Z. Chen, ECE Department and Birck Nanotechnology Center, Purdue University, West Lafayette, Indiana, USA
- IV.B-8 **First Demonstration of Two-Dimensional WS₂ Transistors Exhibiting 105 Room Temperature Modulation and Ambipolar Behavior** 187
11:20 AM W. S. Hwang¹, M. Remskar², R. Yan¹, V. Protasenko¹, K. Tahy¹, S. D. Chae¹, H. Xing¹, A. Seabaugh¹, and D. Jena¹, ¹Department of Electrical Engineering, University of Notre Dame, Notre Dame, Indiana, USA and ²Solid State Physics Department, Jozef Stefan Institute, Ljubljana, SLOVENIA
- IV.B-9 **Low-frequency Noise in Contact and Channel Regions of Ambipolar InAs Nanowire Transistors** 189
11:40 AM C. J. Delker¹, Y. Zi², C. Yang^{2,3}, D. B. Janes¹, ¹School of Electrical and Computer Engineering and Birck Nanotechnology Center, Purdue University, West Lafayette, Indiana, USA, ²Department of Physics, Purdue University, West Lafayette, Indiana, USA, and ³Department of Chemistry, Purdue University, West Lafayette, Indiana, USA

- V.A-1 **High Performance III-V FETs for Low Power CMOS Applications** 193
1:30 PM M. Radosavljevic, Intel Corporation, Technology and Manufacturing Group, Hillsboro, Oregon, USA
- V.A-2 **Vertical InAs Nanowire MOSFETs with $I_{DS} = 1.34$ mA/ μ m and $g_m = 1.19$ mS/ μ m at $V_{DS} = 0.5$ V** 195
2:10 PM K.-M. Persson, M. Berg, M. Borg, J. Wu, H. Sjöland, E. Lind and L.-E. Wernersson, Department of Electrical- and Information Technology, Lund University, Lund, SWEDEN

- V.A-3 **Possible Observation of Ballistic Contact Resistance in Wide Si MOSFETs** 197
2:30 PM A. Majumdar¹ and D. A. Antoniadis², ¹IBM Research Division, T. J. Watson Research Center, Yorktown Heights, New York, USA and ²Department of Electrical Engineering and Computer Science, Massachusetts Institute of Technology, Cambridge, Massachusetts, USA
- V.A-4 **Regrown Ohmic Contacts to InxGa1-xAs Approaching the Quantum Conductivity Limit** 199
2:50 PM J. J. M. Law, A. D. Carter, S. Lee, A. C. Gossard, and M. J. W. Rodwell, ECE and Materials Departments, University of California, Santa Barbara, California, USA
- V.A-5 **Simulation Study of Nanowire Tunnel FETs** 201
3:30 PM A. Schenk¹, R. Rhyner¹, M. Luisier¹, and C. Bessir², ¹Integrated Systems Laboratory, ETH Zürich, Zürich, SWITZERLAND and ²IBM Research-Zürich, Rüschlikon, SWITZERLAND
- V.A-6 **Flicker Noise Characterization and Analytical Modeling of Homo and Hetero-Junction III-V Tunnel FETs** 203
4:10 PM R. Bijesh, D. K. Mohata, H. Liu and S. Datta, The Pennsylvania State University, University Park, Pennsylvania, USA
- V.A-7 **High Current Density InAsSb/GaSb Tunnel Field Effect Transistors** 205
4:30 PM A. W. Dey¹, B. M. Borg², B. Ganjipour², M. Ek³, K. A. Dick^{2,3}, E. Lind¹, P. Nilsson¹, C. Thelander² and L.-E. Wernersson¹, ¹Dept. of Electrical and Information Technology, ²Dept. of Solid State Physics and ³Division of Polymer and Materials Chemistry, Lund University, Lund, SWEDEN
- V.A-8 **Gate-first implant-free InGaAs n-MOSFETs with sub-nm EOT and CMOS-compatible process suitable for VLSI** 207
4:50 PM L. Czornomaz, M. El Kazzi, D. Caimi, C. Rossel, E. Uccelli, M. Sousa, C. Marchiori, M. Richter, H. Siegwart and J. Fompeyrine, IBM Zurich Research Laboratory, Rüschlikon, SWITZERLAND

Session V.B Spin/Memory Devices

209-222

- V.B-1 **Ultrafast Spin Torque Memory Based on Magnetic Tunnel Junctions with Combined In-plane and Perpendicular Polarizers** 211
1:30 PM I. N. Krivorotov¹, G. E. Rowlands¹, T. Rahman², J. A. Katine¹, J. Langer⁴, A. Lyle⁴, H. Zhao², J. G. Alzate⁵, A. A. Kovalev⁶, Y. Tserkovnyak⁶, Z. M. Zeng⁶, H. W. Jiang⁶, K. Galatsis⁵, Y. M. Huai⁷, P. Khalili Amiri⁵, K. L. Wang⁵, and J.-P. Wang², ¹Physics and Astronomy, University of California, Irvine, California, USA, ²Electrical and Computer Engineering, University of Minnesota, Minneapolis, Minnesota, USA, ³Hitachi Global Storage Technologies, San Jose, California, USA, ⁴Singulus Technologies, Kahl am Main, GERMANY, ⁵Electrical Engineering, University of California, Los Angeles, California, USA, ⁶Physics and Astronomy, University of California, Los Angeles, California, USA, and ⁷Avalanche Technology, Fremont, California, USA
- V.B-2 **NanoMagnet Logic** 213
2:10 PM W. Porod, P. Li, F. Shah, M. Siddiq, E. Varga, G. Csaba, V. Sankar, G. H. Bernstein, X. S. Hu, M. Niemier, J. Nahas, and A. Orlov, Center for Nano Science and Technology, University of Notre Dame, Notre Dame, Indiana, USA
- V.B-4 **Nanowire Phase Change Memory with Carbon Nanotube Electrodes** 215
3:30 PM F. Xiong^{1,2,3}, M.-H. Bae^{1,2}, Y. Dai^{1,2}, A. D. Liao², A. Behnam^{1,2}, E. Carrion^{1,2}, S. Hong^{1,2}, D. Ielmini⁴ and E. Pop^{1,2,3}, ¹Micro & Nanotechnology Lab, Univ. Illinois, Urbana-Champaign, Illinois, USA, ²Dept. of Electrical & Computer Engineering, Univ. Illinois, Urbana-Champaign, Illinois, USA, ³Beckman Institute, Univ. Illinois, Urbana-Champaign, Illinois, USA, and ⁴Dipartimento di Elettronica e Informazione, Politecnico di Milano, Milano, ITALY
- V.B-5 **A very reliable multilevel YSZ resistive switching memory** 217
3:50 PM F. Pan, J. Jang, and V. Subramanian, Department of Electrical Engineering and Computer Sciences, University of California, Berkeley, California, USA

V.B-6 **A Comprehensive Model for Crossbar Memory Arrays** 219
4:10 PM A. Chen, Z. Krivokapic, and M.-R. Lin, TD Research, GLOBALFOUNDRIES, Sunnyvale, California, USA

V.B-7 **Spin Neuron for Ultra Low Power Computational Hardware** 221
4:30 PM M. Sharad, G. Panagopoulos and K. Roy, School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA

Rump Sessions 223-224

R.1 **Wells vs. Sheets vs. Tubes** 223
8:30 PM Session Organizers: Joshua Robinson, Penn State and Debdeep Jena, University of Notre Dame

R.2 **Compound semiconductors on Si: "A Happy Marriage" or "Keep Your Filthy Materials Out Of My Fab"?** 223
8:30 PM Session Organizers: Seth Bank, The University of Texas at Austin and Yanning Sun, IBM

Joint DRC/EMC Plenary Session 225-226

8:30 AM **Nonpolar and Semipolar GaN Materials and Devices: The Journey So Far** 225
James S. Speck, University of California, Santa Barbara

Session VI.A Transistor Modeling 227-234

VI.A-1 **Dissipative Quantum Transport in Nanoscale Transistors** 229
10:00 AM J. Guo, Department of ECE, University of Florida, Gainesville, Florida, USA

VI.A-2 **Will Strong Quantum Confinement Effect Limit Low VCC Logic Application of III-V FINFETs?** 231
10:40 AM A.Nidhi¹, V.Saripalli¹, V. Narayanan¹, Y. Kimura², R. Arghavani² and S. Datta¹, ¹The Pennsylvania State University, University Park, Pennsylvania, USA and ²Lam Research, California, USA

VI.A-3 **Exploration of Vertical MOSFET and Tunnel FET Device Architecture for Sub 10nm Node Applications** 233
11:00 AM H. Liu, D. K. Mohata, A. Nidhi, V. Saripalli, V. Narayanan and S. Datta, The Pennsylvania State University, University Park, Pennsylvania, USA

Session VI.B Thin-Film Devices 235-246

VI.B-1 **Organic Thin-Film Transistors for Flexible Displays and Circuits** 237
10:00 AM H. Klauk, Max Planck Institute for Solid State Research, Stuttgart, GERMANY

VI.B-2 **Low-Voltage ZnO Double-Gate Thin Film Transistor Circuits** 239
10:40 AM Y. V. Li^{1,2}, J. I. Ramirez^{1,2}, K. G. Sun^{1,2} and T. N. Jackson^{1,2}, ¹Center for Thin Film Devices and Materials Research Institute and ²Department of Electrical Engineering, Penn State University, University Park, Pennsylvania, USA

VI.B-3 **High Performance Solution-Processed Thin-Film Transistors Based on In₂O₃ Nanocrystals** 241
11:00 AM S. L. Swisher, S. Volkman, K. Braam, J. Jang, and V. Subramanian, Department of Electrical Engineering and Computer Sciences, University of California, Berkeley, California USA

VI.B-4 **Characterization and Modeling of Metal-Insulator Transition (MIT) Based Tunnel Junctions** 243
11:20 AM E. Freeman¹, A. Kar¹, N. Shukla¹, R. Misra¹, R. Engel-Herbert¹, D. Schlom², V. Gopalan¹, K. Rabe³, and S. Datta¹, ¹Pennsylvania State University, Pennsylvania, USA, ²Cornell University, Ithaca, New York, USA, and ³Rutgers University, New Brunswick, New Jersey, USA

VI.B-5 **Two-stage Model for Lifetime Prediction of Highly Stable Amorphous-Silicon Thin-Film Transistors under Low-Gate Field** 245
11:40 AM T. Liu, S. Wagner and J. C. Sturm, Princeton Institute for the Science and Technology of Materials (PRISM), and Department of Electrical Engineering, Princeton University, Princeton, New Jersey, USA

Session VII.A Optoelectronic Devices 247-258

VII.A-1 **Tunnel Injection GaN/AlN Quantum Dot UV LED** 249
1:30 PM J. Verma, P. K. Kandaswamy, V. Protasenko, A. Verma, H. Xing and D. Jena, Department of Electrical Engineering, University of Notre Dame, Notre Dame, Indiana, USA

VII.A-2 **Characterization and Impact of Traps in Lattice-Matched and Strain-Compensated In_{1-x}Ga_xAs/GaAs_{1-y}Sb_y Multiple Quantum Well Photodiodes** 251
1:50 PM W. Chen¹, B. Chen², J. Yuan², A. Holmes², and P. Fay¹, ¹University of Notre Dame, Notre Dame, Indiana, USA and ²University of Virginia, Charlottesville, Virginia, USA

VII.A-3 **InAs Avalanche Photodiode with Improved Electric Field Uniformity** 253
2:10 PM S. J. Maddox¹, W. Sun², Z. Lu², H. P. Nair¹, J. C. Campbell², S. R. Bank², ¹Department of Electrical and Computer Engineering, The University of Texas at Austin, Austin, Texas, USA and ²Department of Electrical and Computer Engineering, University of Virginia, Charlottesville, Virginia, USA

VII.A-4 **278 nm Deep Ultraviolet LEDs with 11% External Quantum Efficiency** 255
2:30 PM M. Shatalov¹, W. Sun¹, A. Lunev¹, X. Hu¹, A. Dobrinsky¹, Y. Bilenko¹, J. Yang¹, M. Shur², R. Gaska¹, C. Moe³, G. Garrett³, and M. Wraback³, ¹Sensor Electronic Technology, Inc., Columbia, South Carolina, USA, ²Department of Electrical, Computer, and Systems Engineering and Center of Integrated Electronics, Rensselaer Polytechnic Institute, New York, USA, and ³U.S. Army Research Laboratory, Adelphi, Maryland, USA

VII.A-5 **Unipolar Barrier-Integrated HgCdTe Infrared Detectors** 257
2:50 PM A. M. Itsuno^{1,3}, J. D. Phillips¹, and S. Velicu², ¹Department of Electrical Engineering, University of Michigan-Ann Arbor, Ann Arbor, Michigan, USA and ²EPIR Technologies, Inc., Bolingbrook, Illinois, USA

VII.A-6 **Late News**
3:10 PM

Session VII.B Biological Devices 259-268

VII.B-1 **Physics and Scaling Prospects of pH-Based Genome Sequencers** 261
1:30 PM J. Go and M. A. Alam, School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA

VII.B-2 **Biologically-inspired Learning Device using Three-terminal Ferroelectric Memristor** 263
1:50 PM M. Ueda¹, Y. Kaneko¹, Y. Nishitani¹, T. Morie² and E. Fujii¹, ¹Advanced Technology Research Laboratory, Panasonic Corporation, Kyoto, JAPAN and ²Graduate School of Life Science and Systems Engineering, Kyushu Institute of Technology, Wakamatsu-ku, Kitakyushu, JAPAN

VII.B-3 **Fabrication and Characterization of Field Effect Reconfigurable Nanofluidic Ionic Diodes: Towards Digitally-Programmed Manipulation of Biomolecules** 265
2:10 PM W. Guan¹, R. Fan², and M. A. Reed^{1,3}, ¹Department of Electrical Engineering, ²Biomedical Engineering, and ³Applied Physics, Yale University, New Haven, Connecticut, USA

VII.B-4 **Transparent Diamond-based Electrolyzer for Integration with Solar Cell** 267
2:30 PM C. Pietzka, Z. Gao, Y. Xu, and E. Kohn, Inst. of Electron Devices and Circuits, Ulm University, Ulm, GERMANY

70th Device Research Conference

Technical Program

Late News

Monday PM, June 18, 2012

Time 4:50 PM Session II.B. Alternate Transistor Concept

Direct Measurement of Dirac Point and Fermi level at Graphene/Oxide interface by Internal Photoemission 269

K. Xu^{1,2}, C. Zeng³, Q. Zhang¹, P. Ye², K. Wang³, C. A. Richter¹, D. Gundlach¹, and N. V. Nguyen¹, ¹Semiconductor and Dimensional Metrology Division, National Institute of Standards and Technology, Gaithersburg, Maryland, USA, ²Purdue University, West Lafayette, Indiana, USA, and ³University of California, Los Angeles, Los Angeles, California, USA

Wednesday AM, June 20, 2012

Time: 11:20 AM Session VI.A.4 Nanoscale Transistors and Modeling

III-V 4D Transistors 271

J. J. Gu¹, X. W. Wang², J. Shao³, A. T. Neal¹, M. J. Manfra³, R. G. Gordon², and P. D. Ye¹, ¹School of Electrical and Computer Engineering, Purdue University, West Lafayette, Indiana, USA, ²Department of Chemistry and Chemical Biology, Harvard University, Cambridge, Massachusetts, USA, and ³Department of Physics, Purdue University, West Lafayette, Indiana, USA

Wednesday AM, June 20, 2012

Time: 11:40 AM Session VI.A.4 Nanoscale Transistors and Modeling

Resonant-Body Silicon Nanowire Field Effect Transistor without Junctions 273

S. T. Bartsch¹, C. Dupré², E. Ollier², and A. M. Ionescu¹, ¹Nanoelectronic Devices Laboratory, Ecole Polytechnique Fédéral de Lausanne (EPFL), Lausanne, SWITZERLAND

Analytic Determination of the Optimum Bandgap for a Tunnel FET 275

Q. Zhang, Y. Lu, C.A. Richter, D. Jena, A. Seabaugh Department of Electrical Engineering, University of Notre Dame, Notre Dame IN 46556, USA

Wednesday PM, June 20, 2012

Time: 2:50 PM Session VII.B BIOLOGICAL AND NOVEL DEVICES

Monolithically Integrated E/D-mode InAlN HEMTs with $f_t/f_{max} > 200/220$ GHz 277

B. Song¹, B. Sensale-Rodriguez¹, R. Wang¹, A. Ketterson², M. Schuette², E. Beam², P. Saunier², X. Gao³, S. Guo³, P. Fay¹, D. Jena¹, and H. G. Xing¹, ¹Department of Electrical Engineering, University of Notre Dame, Notre Dame, USA, ²Triquint Semiconductor, USA, and ³IQE RF LLC, USA